

Title (en)
VACUUM DEPOSITION METHOD

Title (de)
VAKUUMABSCHEIDUNGSVERFAHREN

Title (fr)
PROCEDE DE DEPOT SOUS VIDE

Publication
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Application
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Abstract (en)
[origin: WO2005106070A2] The invention relates to a method for the vacuum deposition of at least one thin layer on a portion of the surface of a substrate. The inventive method is characterised in that it comprises the following steps consisting in: selecting at least one sputtering species which is chemically inactive or active in relation to a material to be sputtered; using at least one linear ion source, which is positioned inside an industrial-size installation, in order to generate a collimated ion beam which mainly comprises the sputtering species; directing the beam towards at least one target based on the material to be sputtered; and positioning at least one portion of the surface of the substrate opposite the target, such that the material sputtered by the ionic bombardment of the target or a material resulting from the reaction of the sputtered material with at least one of the sputtering species is deposited on said portion of surface.

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